

1S2075(K)

Silicon Epitaxial Planar Diode for High Speed Switching

HITACHI

ADE-208-144A (Z)

Rev. 1

Aug. 1995

Features

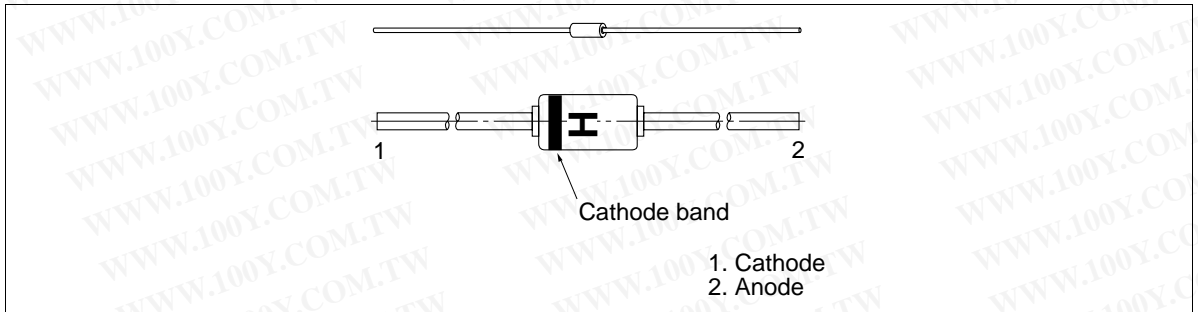
- Low capacitance. ($C = 3.5\text{pF max}$)
- Short reverse recovery time. ($t_{rr} = 8.0\text{ns max}$)
- High reliability with glass seal.

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-34970699
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Ordering Information

Type No.	Cathode band	Mark	Package Code
1S2075(K)	Green	H	DO-35

Outline



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

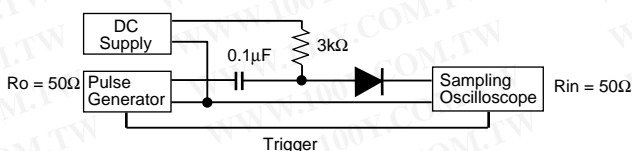
Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	35	V
Reverse voltage	V_R	30	V
Peak forward current	I_{FM}	450	mA
Non-Repetitive peak forward surge current	I_{FSM}^*	600	mA
Average forward current	I_O	100	mA
Power dissipation	P_d	250	mW
Junction temperature	T_j	175	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +175	$^\circ\text{C}$

Note: Within 1s forward surge current.

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.8	V	$I_F = 10\text{mA}$
Reverse current	I_R	—	—	0.1	μA	$V_R = 30\text{V}$
Capacitance	C	—	—	3.5	pF	$V_R = 1\text{V}, f = 1\text{MHz}$
Reverse recovery time	t_{rr}^*	—	—	8.0	ns	$I_F = I_R = 10\text{mA}, I_{rr} = 1\text{mA}$

Note: Reverse recovery time test circuit



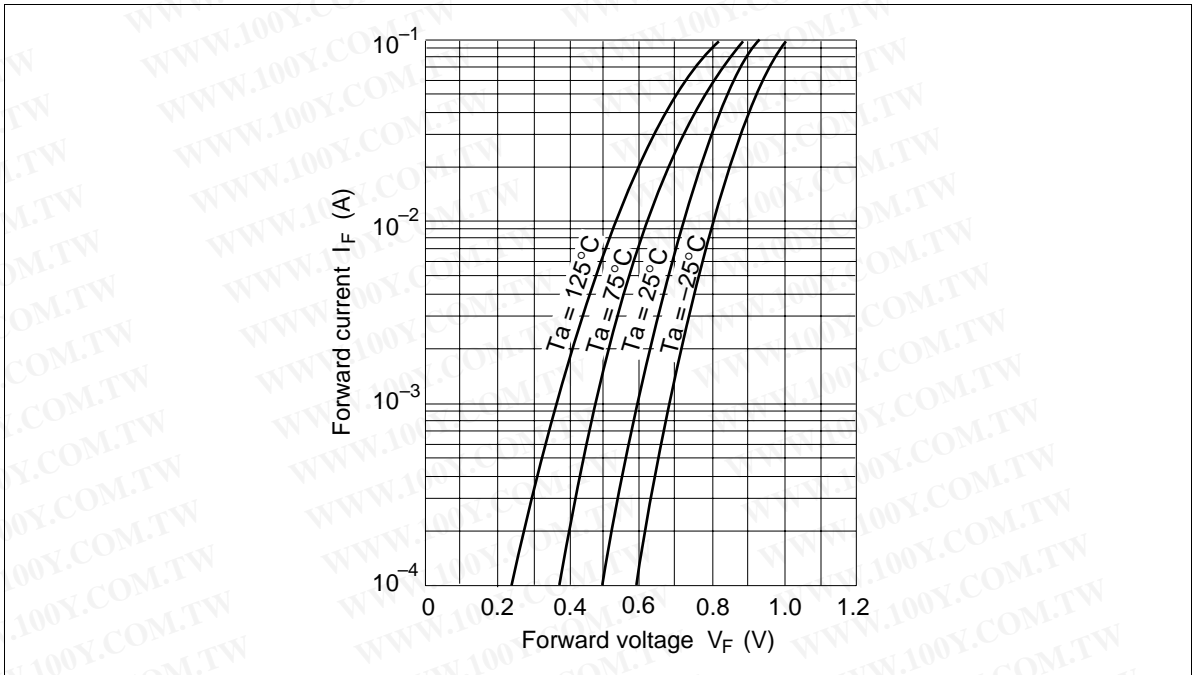


Fig.1 Forward current Vs. Forward voltage

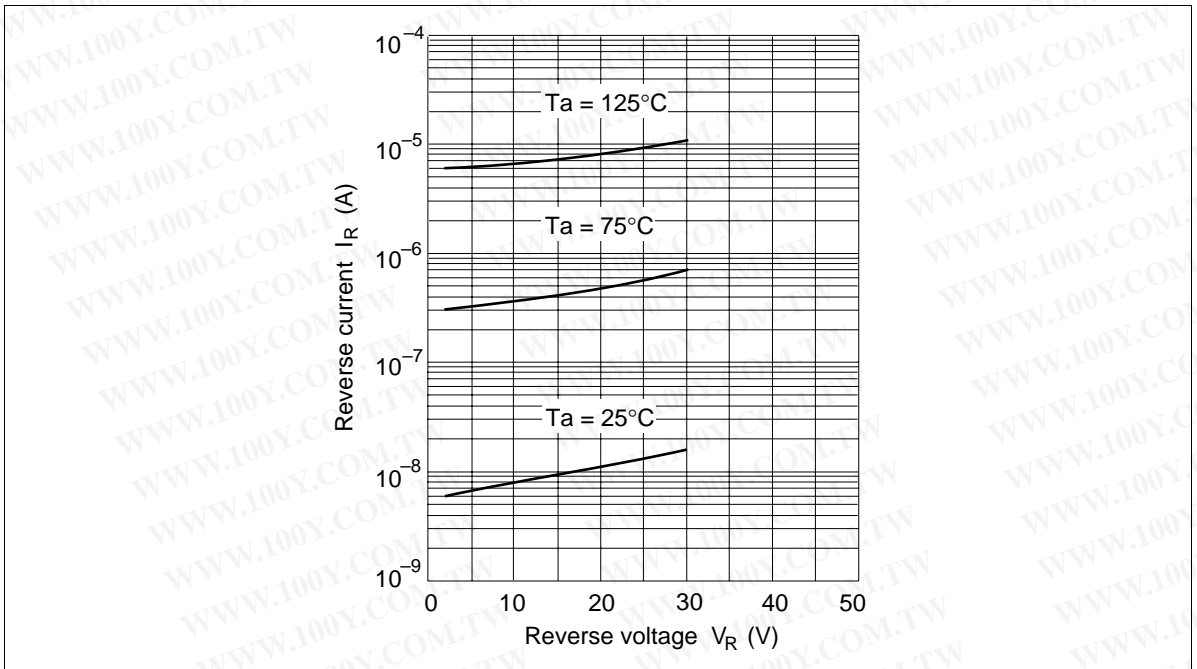


Fig.2 Reverse current Vs. Reverse voltage

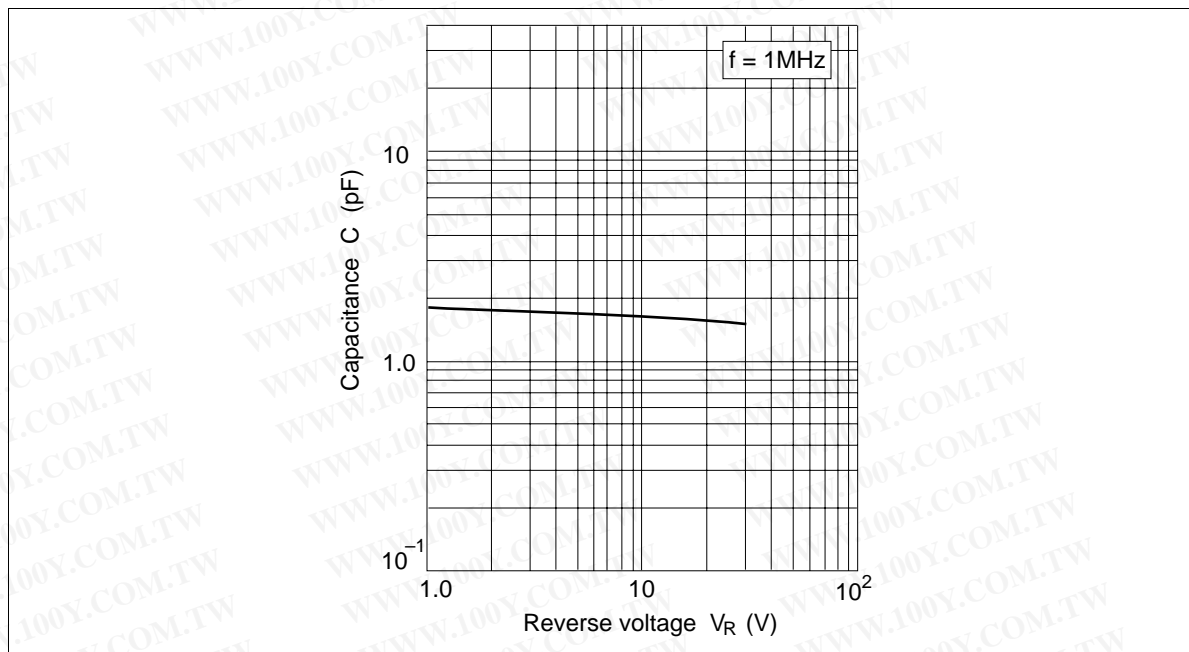
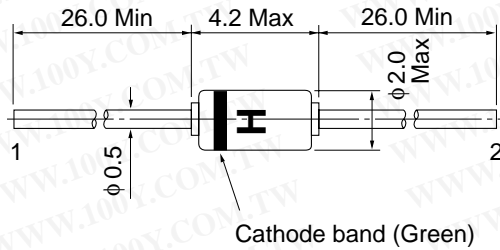


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



- 1 Cathode
- 2 Anode

HITACHI Code	DO-35
JEDEC Code	DO-35
EIAJ Code	SC-48
Weight (g)	0.13

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